

### 155RK SERIES Power Silicon Controlled Rectifiers

Types : 155RK20 TO 155RK160

#### FEATURES

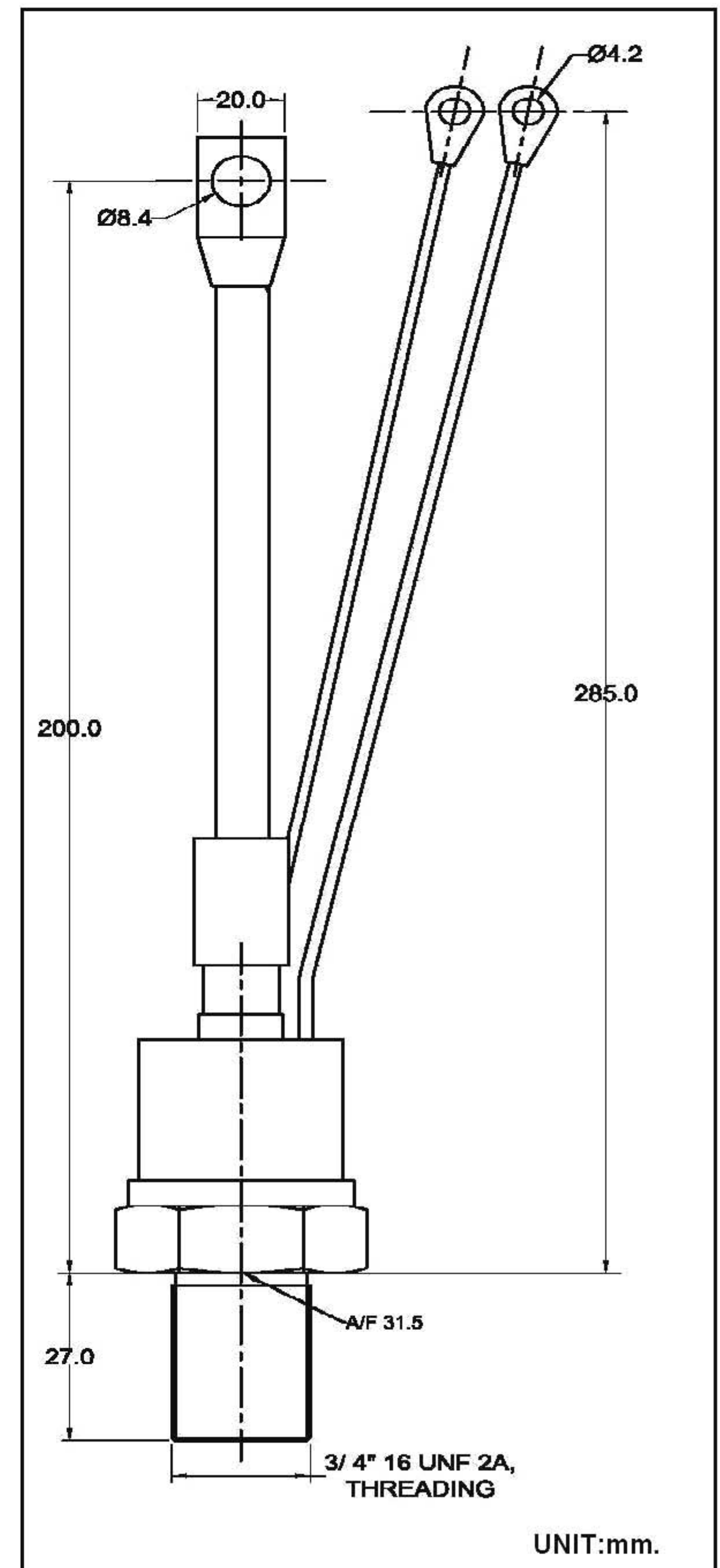
- ❖ Centre amplifying gate.
- ❖ International standard case TO-209AB (TO-93).
- ❖ Threaded studs UNF 3/4 - 16UNF2A.
- ❖ Compression bonded encapsulation for heavy duty operations such as severe thermal cycling.

#### TYPICAL APPLICATIONS

- ❖ DC motor control (e.g. for Machine tools).
- ❖ Controlled rectifiers (e.g. for Battery charging, Uninterrupted Power Supply.).
- ❖ AC controllers (e.g. Temperature control, Lights control).

#### MAJOR RATINGS & CHARACTERISTICS

| Parameters          | 155RK       | Units             |
|---------------------|-------------|-------------------|
| $I_{T(AV)}$         | 150         | A                 |
| @ $T_c$             | 90          | °C                |
| $I_{T(RMS)}$        | 235         | A                 |
| $I_{TSM}$ @ 50 Hz   | 2700        | A                 |
| $I^2t$ @ 50 Hz      | 37          | KA <sup>2</sup> s |
| $V_{DRM} / V_{RRM}$ | 200 to 1600 | V                 |
| $t_q$ typical       | 100         | μs                |
| $T_J$               | -40 to 125  | °C                |



# SILICON CONTROLLED RECTIFIERS

## 155RK SERIES

### ELECTRICAL SPECIFICATION VOLTAGE RATINGS

| Type Number | Voltage Code | $V_{RRM} / V_{DRM}$ max. repetitive peak and off-state voltage<br>V | $V_{RSM}$ max. non-repetitive peak voltage<br>V | $I_{DRM} / I_{RRM}$ max. @ 125°C<br>mA |
|-------------|--------------|---------------------------------------------------------------------|-------------------------------------------------|----------------------------------------|
| 155RK       | 20           | 200                                                                 | 300                                             | 30                                     |
|             | 40           | 400                                                                 | 500                                             |                                        |
|             | 60           | 600                                                                 | 700                                             |                                        |
|             | 80           | 800                                                                 | 900                                             |                                        |
|             | 100          | 1000                                                                | 1100                                            |                                        |
|             | 120          | 1200                                                                | 1300                                            |                                        |
|             | 140          | 1400                                                                | 1500                                            |                                        |
|             | 160          | 1600                                                                | 1700                                            |                                        |

### ON-STATE CONDUCTION

|              | Parameter                                        | 155RK | Units             | Conditions                                                    |
|--------------|--------------------------------------------------|-------|-------------------|---------------------------------------------------------------|
| $I_{T(AV)}$  | Max. average on-state current @ case temperature | 150   | A                 | 180°C conduction, half sine wave                              |
|              |                                                  | 90    | °C                |                                                               |
| $I_{T(RMS)}$ | Max. RMS on-state current                        | 235   |                   |                                                               |
| $I_{TSM}$    | Max. peak one cycle non-repetitive surge current | 2700  | A                 | t = 10ms<br>Sinusoidal half wave,<br>Initial $T_J = T_J$ max. |
| $I^2t$       | Maximum $I^2t$ for fusing                        | 37    | kA <sup>2</sup> s | t = 10ms                                                      |
| $V_{T(TO)}$  | Threshold voltage                                | 1.14  | V                 | $T_J = T_J$ max.                                              |
| $r_t$        | On-state slope resistance                        | 1.7   | mΩ                | $T_J = T_J$ max.                                              |
| $V_{TM}$     | Max. on state voltage                            | 1.8   | V                 | $I_{pk} = 471A$ , $T_J = 125°C$ , $t_p = 10ms$ sine pulse     |
| $I_H$        | Maximum holding current                          | 300   | mA                | $T_J = 25°C$ , anode supply 12V resistive load                |
| $I_L$        | Latching current                                 | 600   |                   |                                                               |

### SWITCHING

|       | Parameter                                             | 155RK | Units | Conditions                                                                                                                  |
|-------|-------------------------------------------------------|-------|-------|-----------------------------------------------------------------------------------------------------------------------------|
| di/dt | Max. non-repetitive rate of rise of turned-on current | 100   | A/μs  | Gate drive 20V, 20Ω, $t_r \leq 1\mu s$<br>$T_J = 125°C$ , anode voltage $\leq 80\% V_{DRM}$                                 |
| $t_d$ | Typical delay time                                    | 1.0   | μs    | Gate current 1A, $di_g/dt = 1A/\mu s$<br>$V_d = 0.67\% V_{DRM}$ , $T_J = 25°C$                                              |
| $t_q$ | Typical turn-off time                                 | 100   |       | $I_{TM} = 300A$ , $T_J = 125°C$ , $di/dt = 20A/\mu s$ , $V_R = 50V$<br>$dv/dt = 20V/\mu s$ , Gate 0V 100Ω, $t_p = 500\mu s$ |

# SILICON CONTROLLED RECTIFIERS

## 155RK SERIES

### ELECTRICAL SPECIFICATION

#### BLOCKING

|                                      | Parameter                                          | 155RK | Units | Conditions                                                                |
|--------------------------------------|----------------------------------------------------|-------|-------|---------------------------------------------------------------------------|
| dv/dt                                | Maximum critical rate of rise of off-state voltage | 500   | V/μs  | T <sub>J</sub> = 125°C, linear to 80% rated V <sub>DRM</sub>              |
| I <sub>RRM</sub><br>I <sub>DRM</sub> | Max. peak reverse and off-state leakage current    | 30    | mA    | T <sub>J</sub> = 125°C, rated V <sub>DRM</sub> / V <sub>RRM</sub> applied |

#### TRIGGERING

|                    | Parameter                           | 155RK |      | Units | Conditions                                                                                                                                                                   |
|--------------------|-------------------------------------|-------|------|-------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| P <sub>GM</sub>    | Maximum peak gate power             | 10.0  |      | W     | T <sub>J</sub> = 125°C, t <sub>p</sub> ≤ 5ms                                                                                                                                 |
| P <sub>G(AV)</sub> | Maximum average gate power          | 2.0   |      |       | T <sub>J</sub> = 125°C, f = 50Hz, d% = 50                                                                                                                                    |
| I <sub>GM</sub>    | Max. peak positive gate current     | 3.0   |      | A     | T <sub>J</sub> = 125°C, t <sub>p</sub> ≤ 5ms                                                                                                                                 |
| +V <sub>GM</sub>   | Max. peak positive gate voltage     | 20    |      | V     | T <sub>J</sub> = 125°C, t <sub>p</sub> ≤ 5ms                                                                                                                                 |
| -V <sub>GM</sub>   | Max. peak negative gate voltage     | 5.0   |      |       |                                                                                                                                                                              |
| I <sub>GT</sub>    | DC gate current required to trigger | TYP.  | MAX. | mA    | T <sub>J</sub> = 25°C<br>Max. required gate trigger / current / voltage are the lowest value which will trigger all units 12V anode-to-cathode applied.                      |
|                    |                                     | 90    | 150  |       |                                                                                                                                                                              |
| V <sub>GT</sub>    | DC gate voltage required to trigger | 1.8   | 3.0  | V     | T <sub>J</sub> = 25°C                                                                                                                                                        |
| I <sub>GD</sub>    | DC gate current not to trigger      | 10    |      | mA    | T <sub>J</sub> = 125°C<br>Max. gate current / voltage not to trigger is the max. value which will not trigger any unit with rated V <sub>DRM</sub> anode-to-cathode applied. |
| V <sub>GD</sub>    | DC gate voltage not to trigger      | 0.25  |      |       |                                                                                                                                                                              |

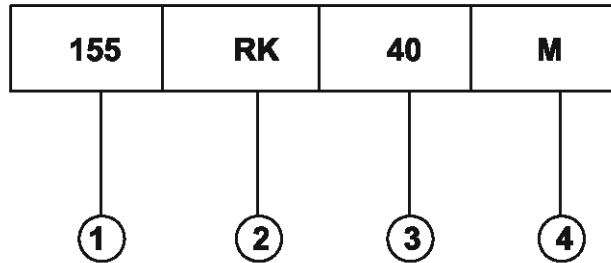
#### THERMAL AND MECHANICAL SPECIFICATION

|                   | Parameter                                  | 155RK               | Units | Conditions                                 |
|-------------------|--------------------------------------------|---------------------|-------|--------------------------------------------|
| T <sub>J</sub>    | Max. operating temperature range           | -40 to 125          | °C    |                                            |
| T <sub>stg</sub>  | Max. storage temperature range             | -40 to 150          |       |                                            |
| R <sub>thJC</sub> | Max. thermal resistance, junction to case  | 0.11                | K/W   | DC operation                               |
| R <sub>thCS</sub> | Max. thermal resistance, case to heat sink | 0.04                |       | Mounting surface, smooth, flat and greased |
| T                 | Mounting force, ±10%                       | 48.5                | Nm    | Non lubricated threads                     |
|                   |                                            | 24.5                |       | Lubricated threads                         |
| wt                | Approximate weight                         | 535                 | gm    |                                            |
|                   | Case style                                 | To - 209AE (TO-118) |       | See outline                                |

# SILICON CONTROLLED RECTIFIERS

---

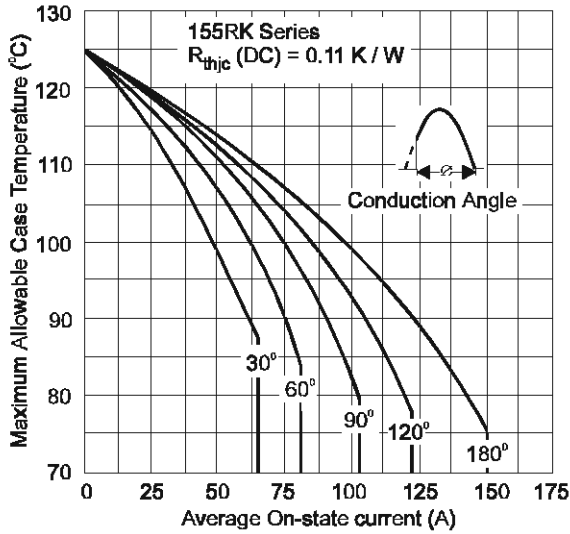
## ORDER INFORMATION TABLE



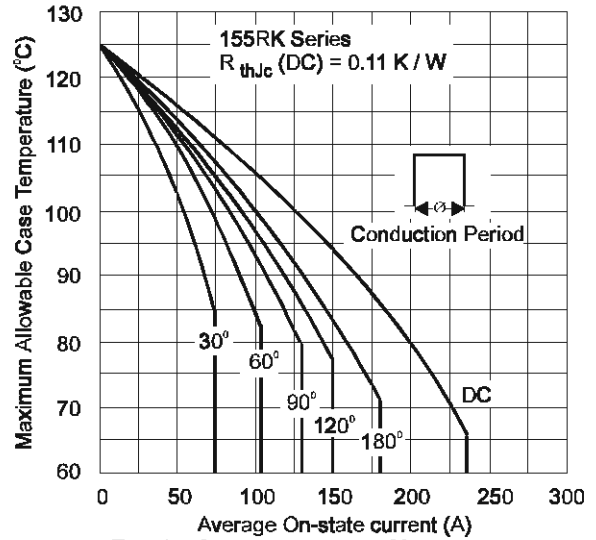
- ① - Current Code
- ② - RK - Essential part number
- ③ - Voltage Rating (See table)
- ④ - None - Stud 3/4" 16UNF 2A Threading  
M - Stud M20 x 1.5P Metric Threading

# SILICON CONTROLLED RECTIFIERS

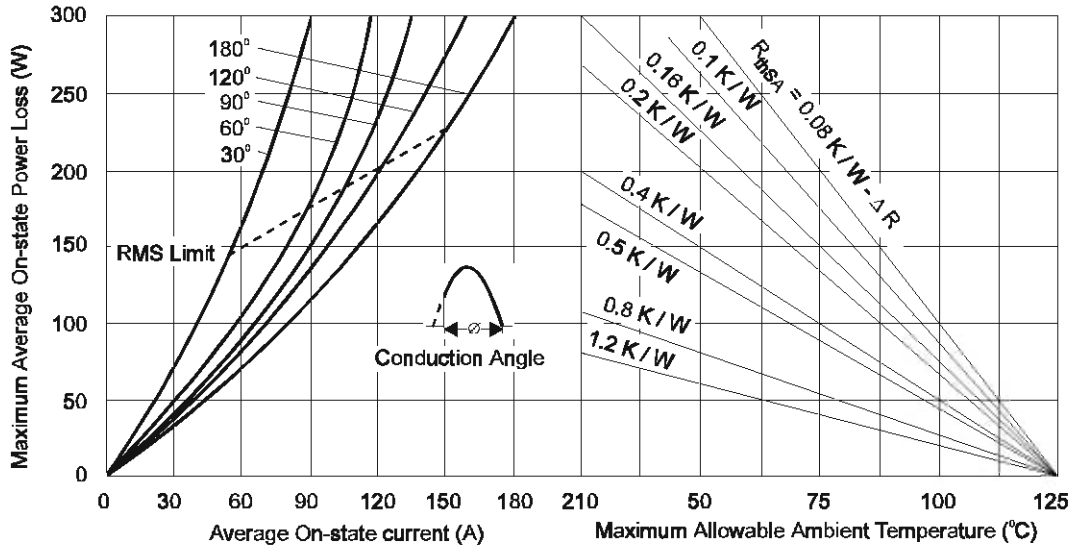
## 155RK SERIES



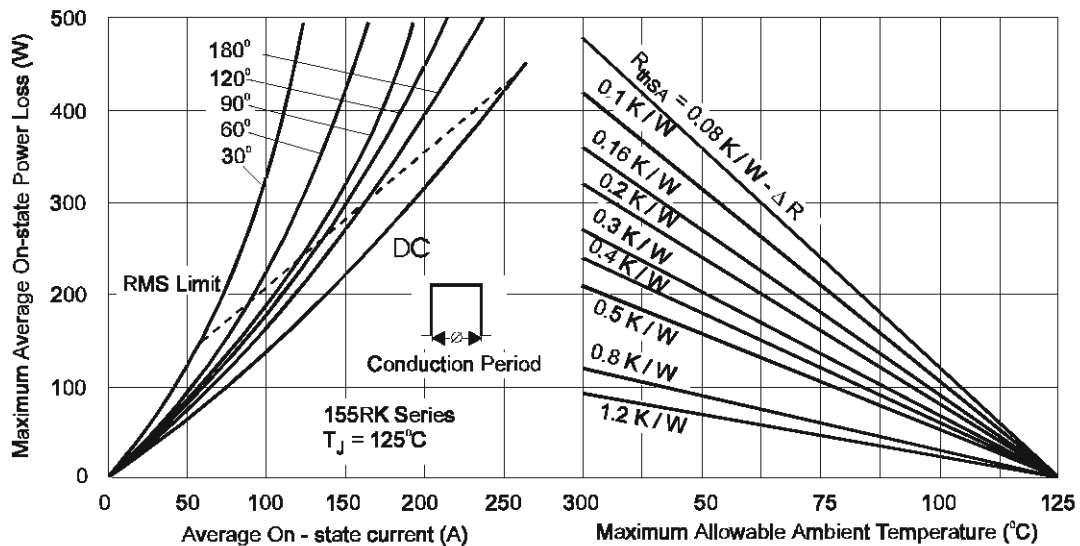
**Fig. 1 - Current Ratings Characteristics**



**Fig. 2 - Current Ratings Characteristics**



**Fig. 3 - On-state Power Loss Characteristics**



**Fig. 4 - On-state Power Loss Characteristics**

# SILICON CONTROLLED RECTIFIERS

## 155RK SERIES

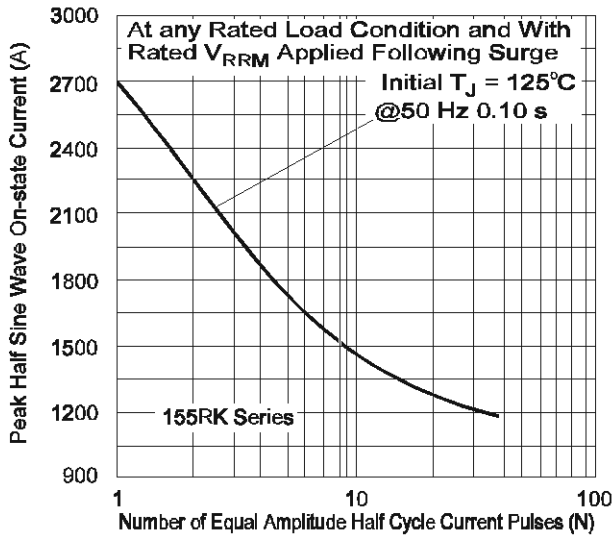


Fig. 5 - Maximum Non-Repetitive Surge Current

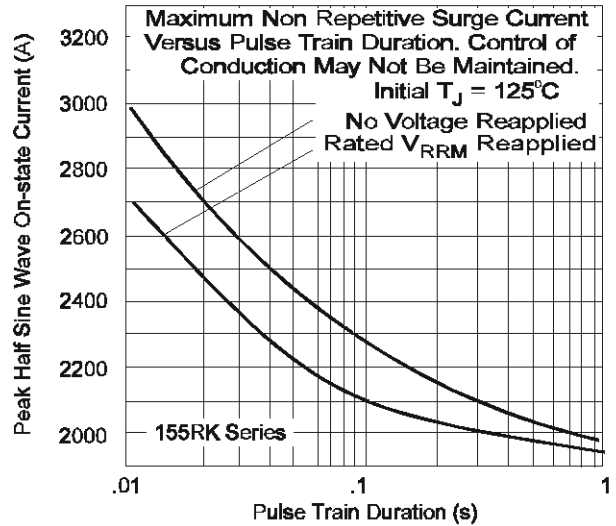


Fig. 6 - Maximum Non-Repetitive Surge Current

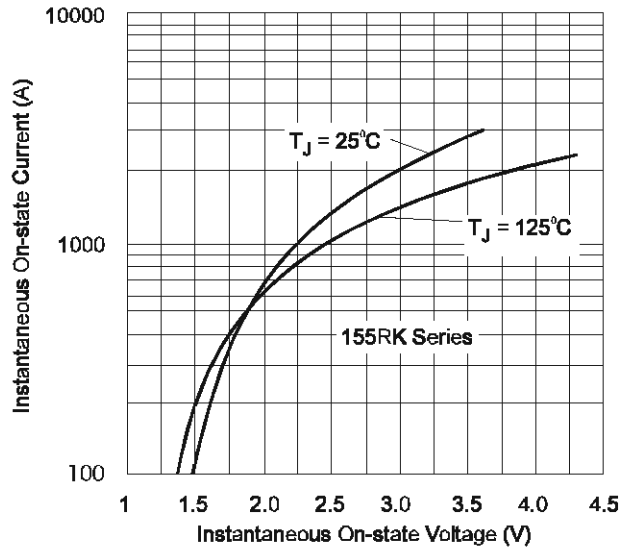


Fig. 7 - On-state Voltage Drop Characteristics

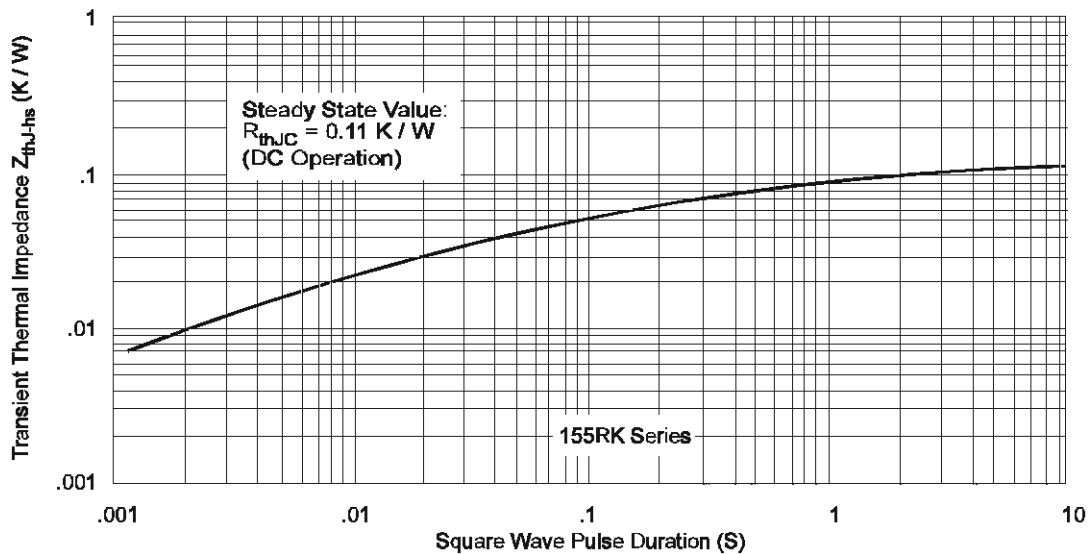


Fig. 8 - Thermal Impedance  $Z_{thJ-hs}$  Characteristics

# SILICON CONTROLLED RECTIFIERS

## 155RK SERIES

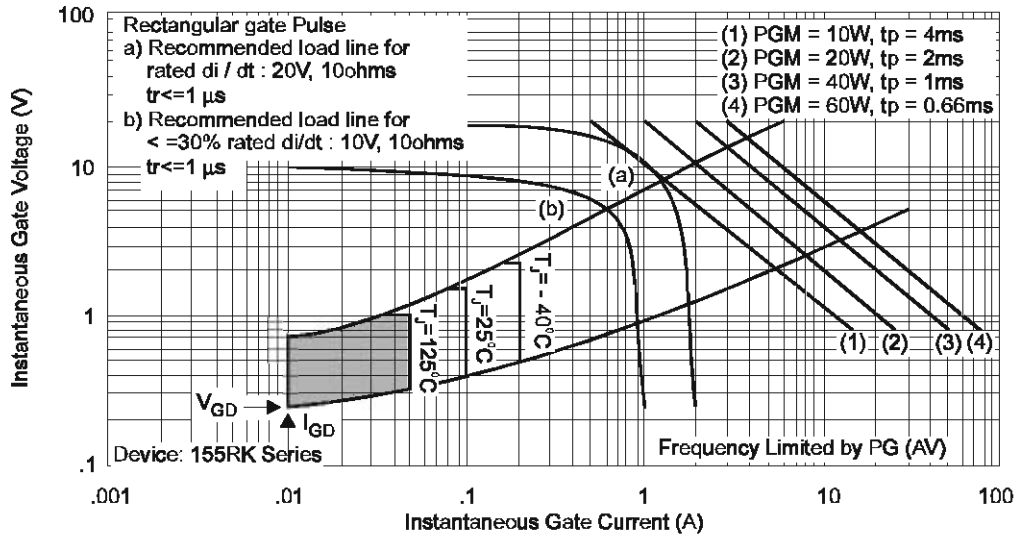


Fig. 9 - Gate Characteristics